

Supplementary

Growth and improved magnetoelectric response of strain modified Aurivillius SrBi_{4.25}La_{0.75}Ti₄FeO₁₈ thin films

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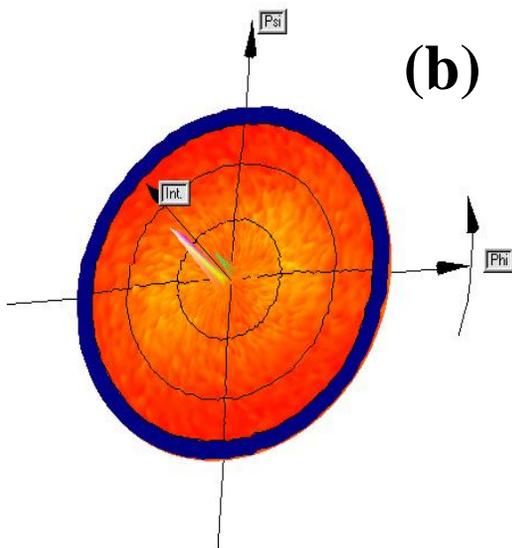
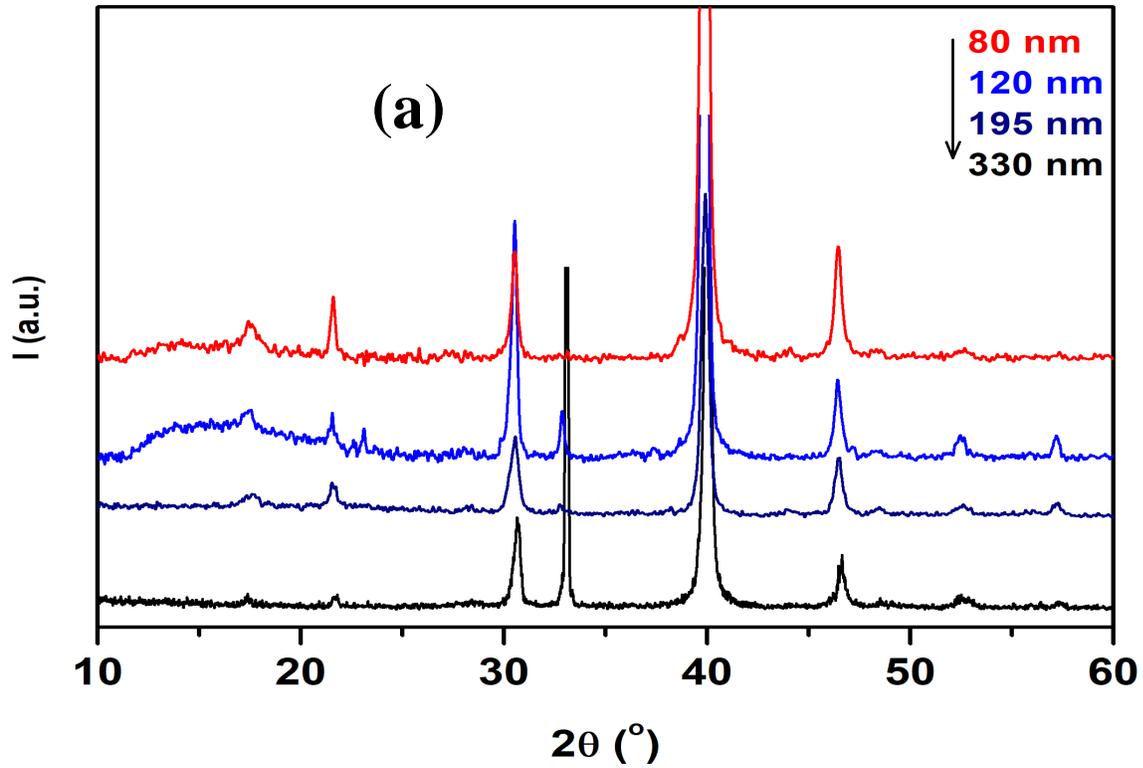
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Fig. S1 (a) GIXRD scans of SBLFT/Pt/TiO₂/SiO₂/Si thin films grown at optimized conditions of 560 °C at 100-mTorr oxygen partial pressure with different thicknesses. (b) Pole figure for SBLFT grown at 560 °C.



2Theta: 32.9100

Intensities:

	Psi	Phi	Intensity
Min	81.0	130.5	1.000
Max	6.0	238.5	198.500

Dimension: 2.5D

Scale: Linear

Color map: Standard

Contours: 10

	Intensity	Color
1	18.955	Red
3	54.864	Orange
5	90.773	Yellow
7	126.682	Green
10	180.545	Blue

Grid settings:

	Psi	Phi
First	0	0
Last	90	360
Step	30	90

Fig. S2 Grain morphology of SBLFT thin films, observed by FESEM, for samples with a thickness of (a) 80 nm, (b) 120 nm and (c) 330 nm and (d) ceramic SBLFT target used for thin film deposition.

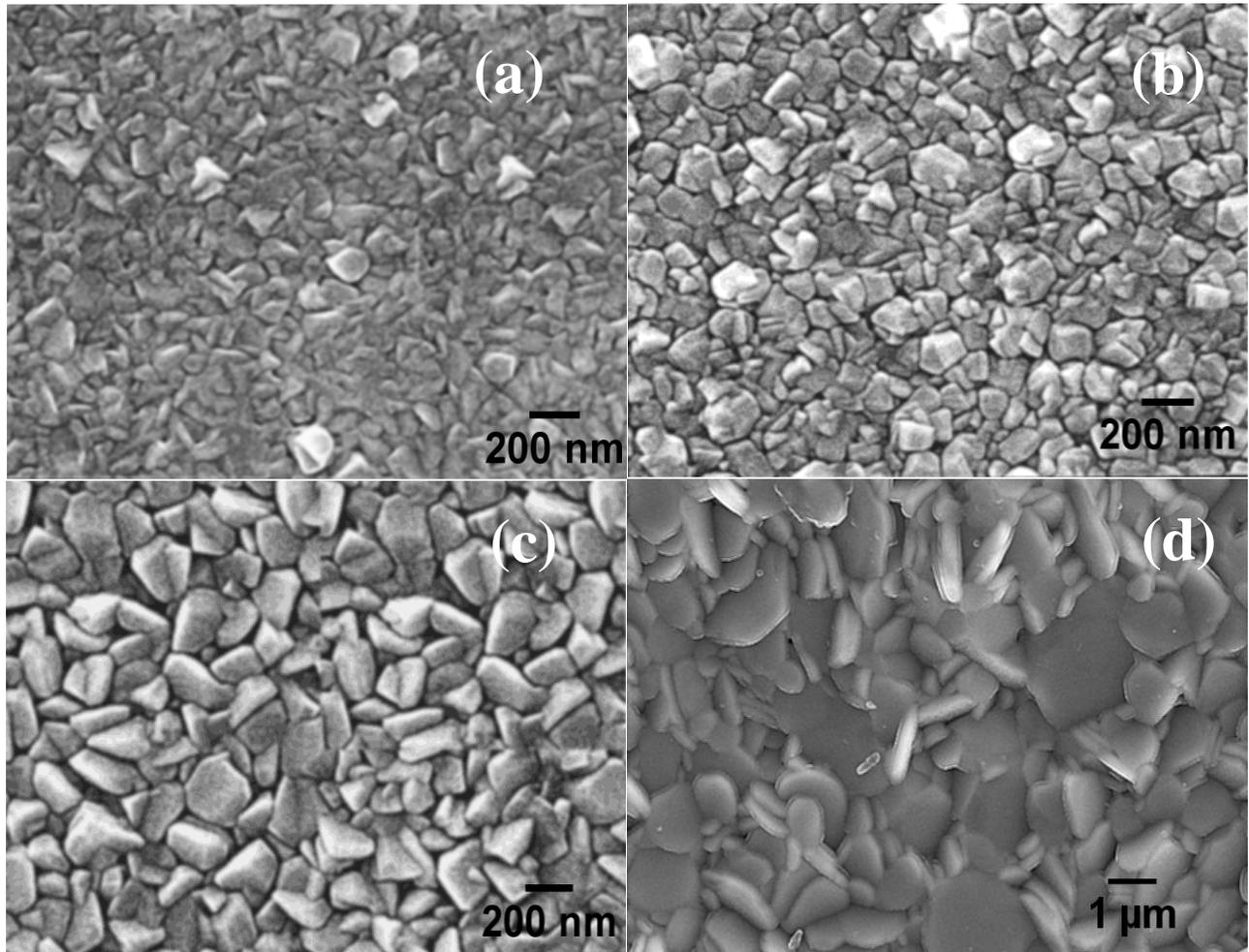


Fig. S3 Ferroelectric – paraelectric phase transition (T_C) is at 340 °C and high temperature maxima (T_m) is at 470 °C. This T_m can be related to the ferroelastic – paraelastic phase transition.

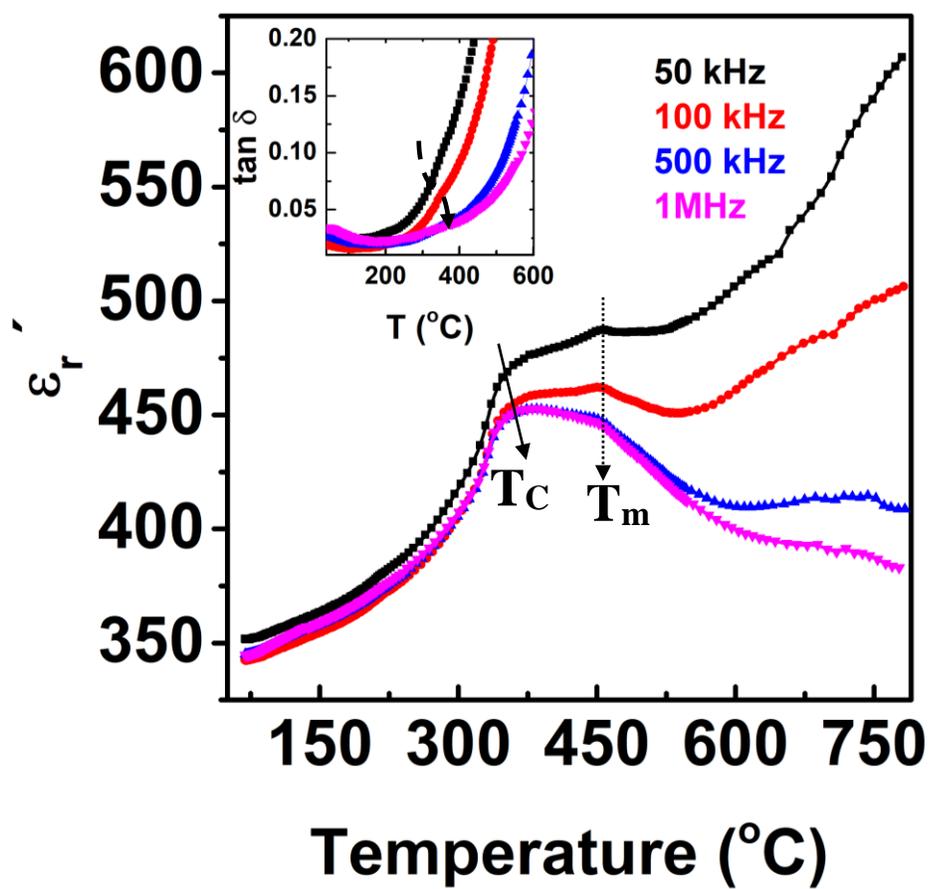


Fig. S4 EELS spectrum displaying the Bi-N_{4,5}, Ti-L_{2,3}, O-K; Fe-L_{2,3}, and La-M_{4,5} edges.

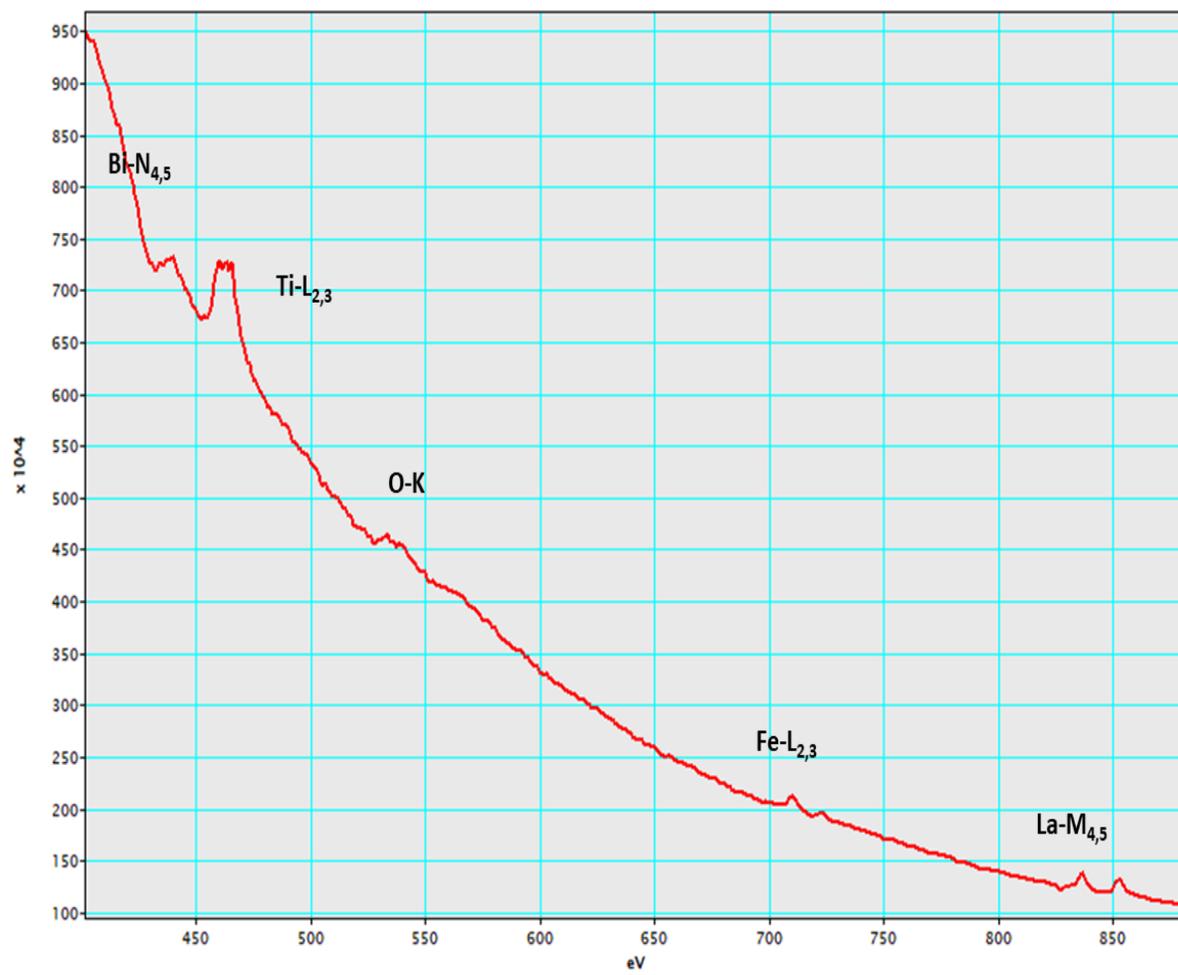


Fig. S5 (a) STEM ADF micrograph. The green square highlights the area used to perform the SR-EELS analysis. (b) DF micrograph acquired simultaneously as the SR-EELS spectra (c) Bi chemical map (d) EELS spectrum displaying the Bi-M_{4,5} edges.

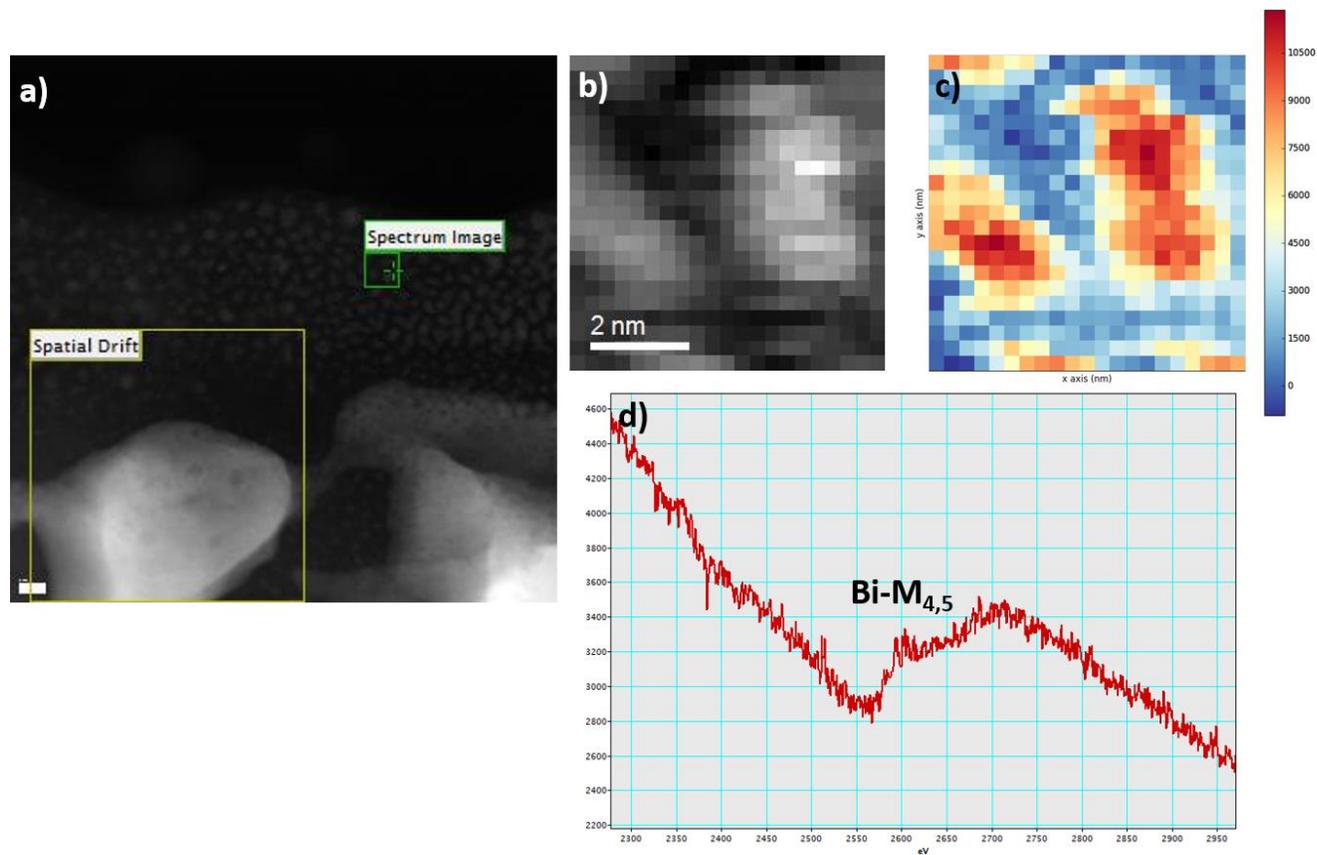


Fig. S5 (e) O/Fe ratio variation close to a nanoregions

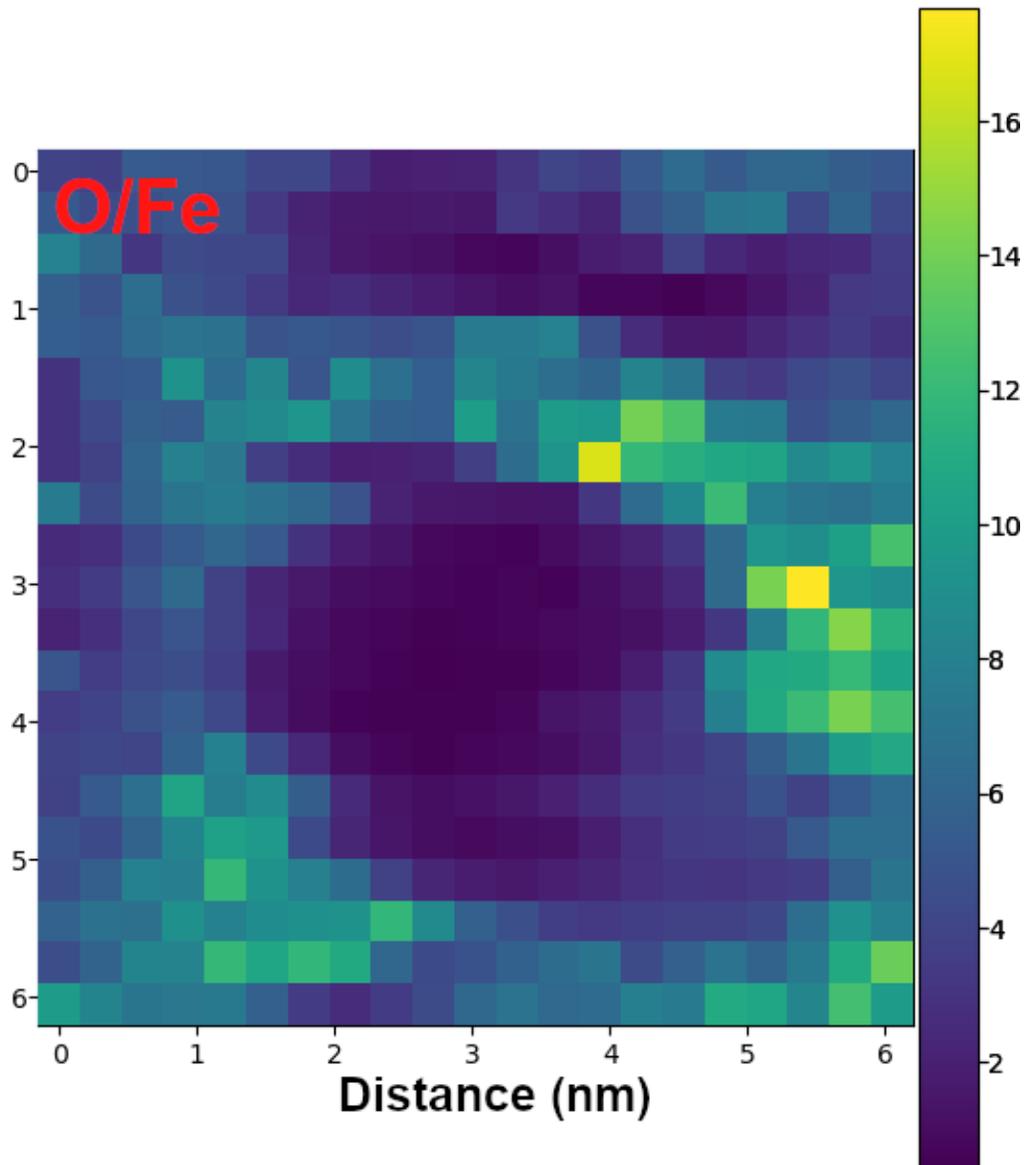


Fig. S6 (a) Polarization – electric field hysteresis loops of SBLFT thin films with different thickness and (b) P_r and E_C relation as a function of thickness.

